

Silicon PNP Power Transistors

2SB1094

DESCRIPTION

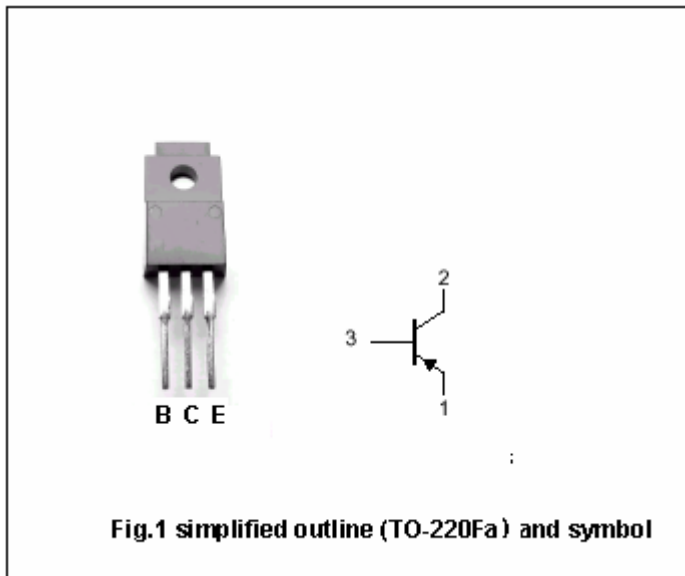
- With TO-220Fa package
- Complement to type 2SD1585

APPLICATIONS

- Ideal for power supplies or variety or in audio and other equipment

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-60	V
V <sub>CEO</sub>	Collector -emitter voltage	Open base	-60	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-7	V
I <sub>C</sub>	Collector current		-3	A
I <sub>CM</sub>	Collector current-peak		-5	A
I <sub>B</sub>	Base current		-0.6	A
P <sub>C</sub>	Collector power dissipation	T <sub>a</sub> =25°C	2.0	W
		T <sub>C</sub> =25°C	15	
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO</sub>	Collector-emitter voltage	I <sub>C</sub> =-30mA; I <sub>B</sub> =0	-60			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-2A ; I <sub>B</sub> =-0.2A			-1.5	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-2A ; I <sub>B</sub> =-0.2A			-2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-60V; I <sub>E</sub> =0			-10	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-7V; I <sub>C</sub> =0			-10	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-50mA ; V <sub>CE</sub> =-5V	20			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-0.5A ; V <sub>CE</sub> =-5V	40		200	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.1A; V <sub>CE</sub> =-5V		20		MHz
C <sub>OB</sub>	Collector output capacitance	f=1MHz ; V <sub>CB</sub> =-10V		70		pF

◆ h<sub>FE-2</sub> Classifications

M	L	K
40-80	60-120	100-200

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PACKAGE OUTLINE

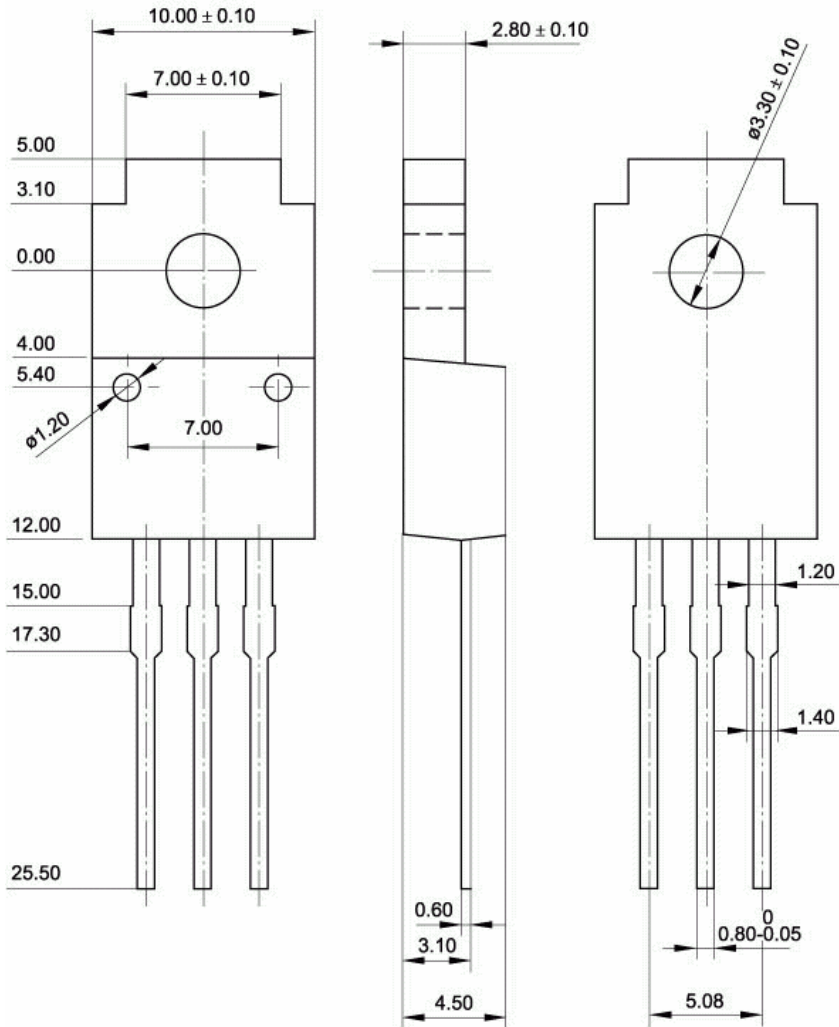


Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.15$  mm)